| | Type | Ref # | Hits | Search Text | DBs | Time Stamp | Comments | Error Definition | Errors |
|---|---|---|---|---|---|---|---|---|---|
| 1 | BRS | S1 | 55939 | etch$3 and (transistor or MOS or memory or bitline or dram or "dynamic random access memory" or capacitor) and ((contact adj (hole or open$3)) or sac or (self adj align$4)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/18 17:21 | | | |
| 2 | BRS | S2 | 43318 | etch$3 and (transistor or MOS or memory or bitline or dram or "dynamic random access memory" or capacitor) and gate and ((contact adj (hole or open$3)) or sac or (self adj align$4)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/18 17:21 | | | |
| 3 | BRS | S3 | 9402 | etch$3 same (transistor or MOS or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/18 17:24 | | | |
| 4 | BRS | S4 | 7410 | S3 and @pd<="20040220" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/18 17:24 | | | |
| 5 | BRS | S5 | 8862 | etch$3 same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/18 17:25 | | | |
| 6 | BRS | S6 | 6970 | S5 and @pd<="20040220" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/18 17:26 | | | |
| 7 | BRS | S7 | 1704 | (etch$3 same (plasma or gas or dry)) same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/18 19:12 | | | |

| | Type | Ref # | Hits | Search Text | DBs | Time Stamp | C mments | Err r Definiti n | Errors |
|---|---|---|---|---|---|---|---|---|---|
| 8 | BRS | S8 | 1292 | S7 and @pd<="20040220" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:14 | | | |
| 9 | BRS | S9 | 5678 | S6 not S8 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 18:19 | | | |
| 10 | BRS | S10 | 37 | (etch$3 same (plasma or gas or dry)) same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4)) same capp$3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:16 | | | |
| 11 | BRS | S11 | 28 | S10 and @pd<="20040220" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:17 | | | |
| 12 | BRS | S12 | 8862 | etch$3 same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:17 | | | |
| 13 | BRS | S13 | 224 | etch$3 same (transistor or memory or bitline or dram or "dynamic random access memory" or capacitor) same gate same ((contact adj (hole or open$3)) or sac or (self adj align$4)) same capp$3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:17 | | | |
| 14 | BRS | S14 | 166 | S13 and @pd<="20040220" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:29 | | | |

|  | Type | Ref # | Hits | Search Text | DBs | Time Stamp | Comments | Err r Definition | Err rs |
|---|---|---|---|---|---|---|---|---|---|
| 15 | BRS | S15 | 131 | CHEN-YI-NAN.in. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:32 | | | |
| 16 | BRS | S16 | 39 | HUANG-TSE-YAO.in. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:34 | | | |
| 17 | BRS | S17 | 32 | MAO-HUI-MIN.in. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | 2005/10/ 18 19:34 | | | |